



JR0205 Series Sensitive gate SCRs

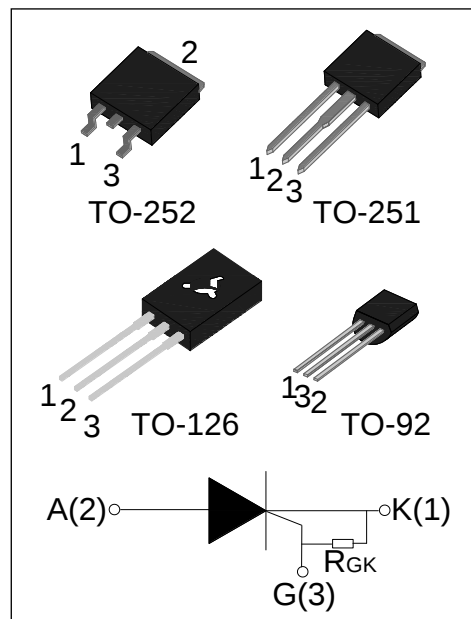
Rev.2.0

DESCRIPTION:

The JR0205 SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
I_{GT}	≤ 200	μA
V_{TM}	≤ 1.5	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-110	$^{\circ}C$
Repetitive peak off-state voltage		V_{DRM}	600	V
Repetitive peak reverse voltage		V_{RRM}	600	V
RMS on-state current	TO-92 ($T_C=60^{\circ}C$)	$I_{T(RMS)}$	2	A
	TO-251/ TO-252/ TO-126 ($T_C=72^{\circ}C$)			
Non repetitive surge peak on-state current (tp=10ms)		I_{TSM}	20	A
I^2t value for fusing (tp=10ms)		I^2t	2	A^2s
Critical rate of rise of on-state current		di/dt	50	$A/\mu s$
Peak gate current (tp=20 μs , $T_j=110^{\circ}C$)		I_{GM}	0.2	A
Peak gate power (tp=20 μs , $T_j=110^{\circ}C$)		P_{GM}	0.5	W
Average gate power dissipation($T_j=110^{\circ}C$)		$P_{G(AV)}$	0.1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	-	40	200	μA
V_{GT}		-	0.5	0.8	V
V_{GD}	$V_D=V_{DRM}$ $T_j=110^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	3	mA
I_H	$I_T=0.05\text{A}$	-	-	2	mA
dV/dt	$V_D=60\%V_{DRM}$ $T_j=110^{\circ}\text{C}$ $R_{GK}=1\text{K}\Omega$	10	-	-	$\text{V}/\mu\text{s}$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=4\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=110^{\circ}\text{C}$	100	μA

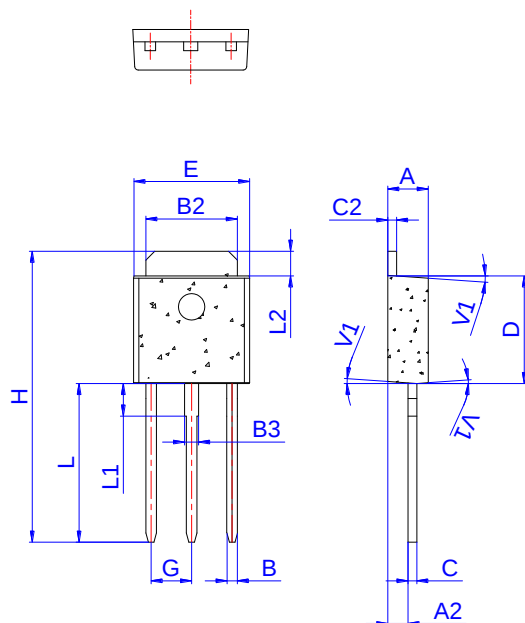
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-92	20	$^{\circ}\text{C}/\text{W}$
		TO-251/ TO-252/ TO-126	10	

ORDERING INFORMATION

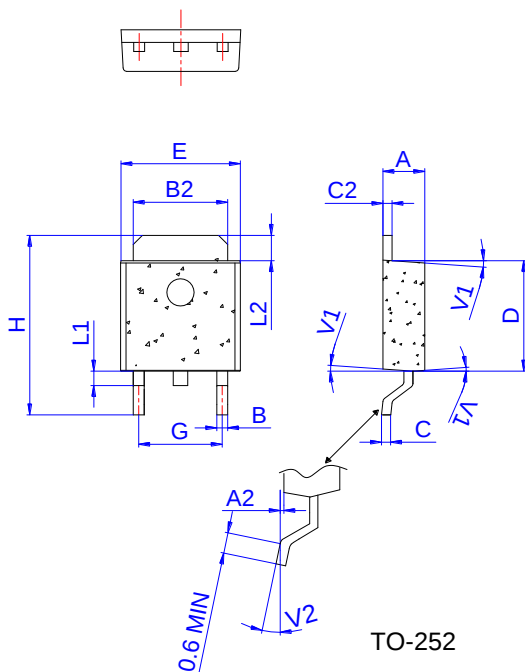
J R 02 05 H JieJie Microelectronics Co.,Ltd Sensitive gate SCRs $I_{T(RMS)}:2\text{A}$ 05:$I_{GT} \leq 200\mu\text{A}$ H:TO-251 K:TO-252 U:TO-92 Q:TO-126				
--	--	--	--	--

PACKAGE MECHANICAL DATA



TO-251

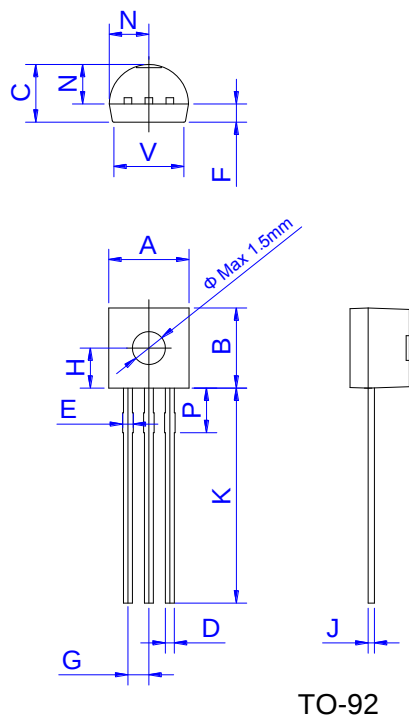
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



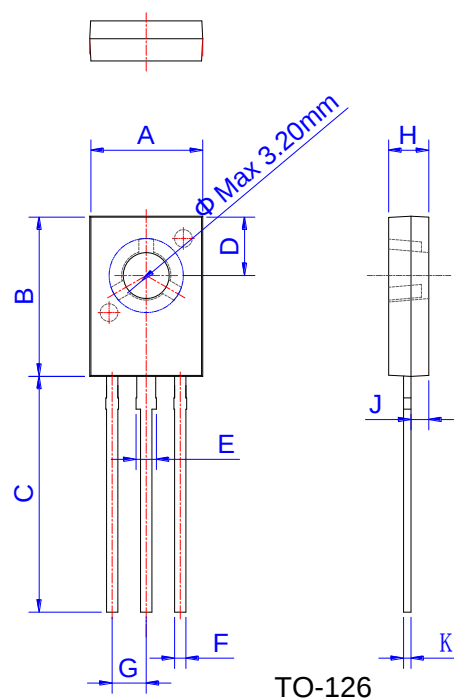
TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

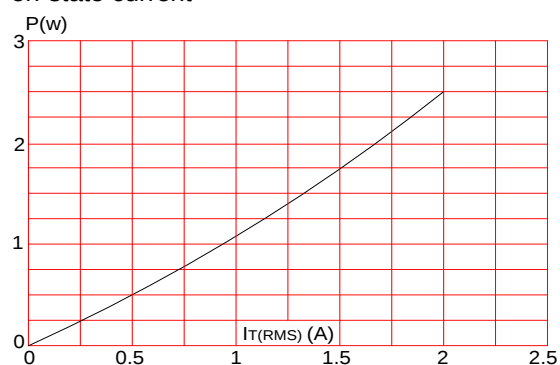
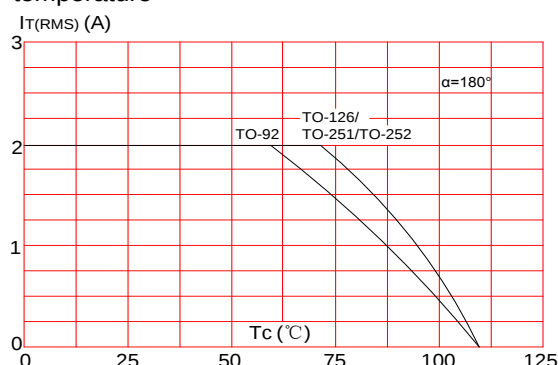
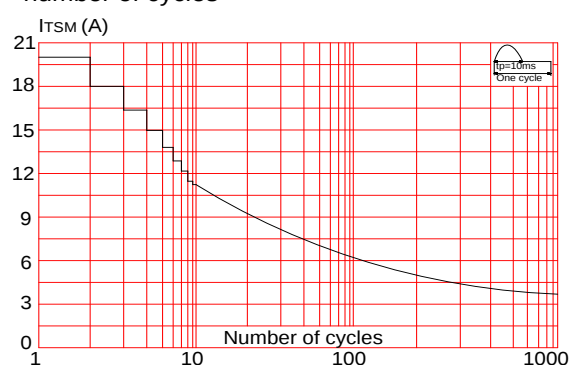
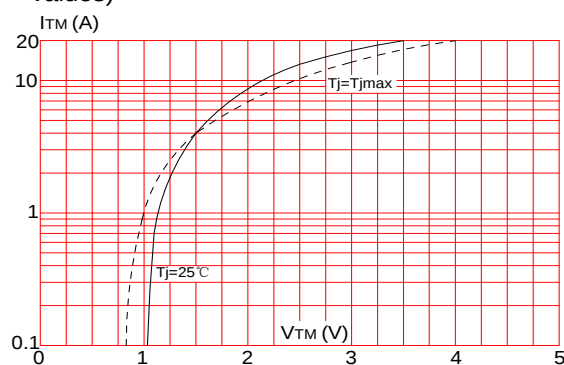
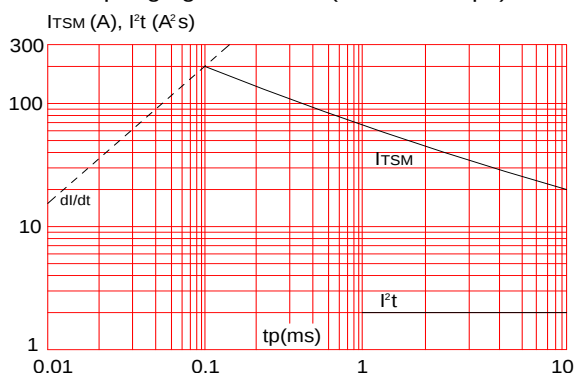
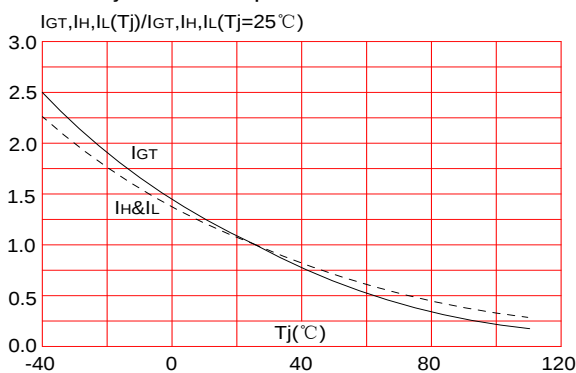
PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.60		0.80	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

FIG.1 Maximum power dissipation versus RMS on-state current**FIG.2** RMS on-state current versus case temperature**FIG.3** Surge peak on-state current versus number of cycles**FIG.4** On-state characteristics (maximum values)**FIG.5** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)**FIG.6** Relative variations of gate trigger current, holding current and latching current versus junction temperature

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document is the second version which is made in 19-Nov.-2014. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.

Copyright ©2014 Jiangsu JieJie Microelectronics Co.,Ltd. Printed All rights reserved.